



NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI CBSL1** is Designed for UHF Class A Amplifier Applications in Cellular Base Station Equipment.

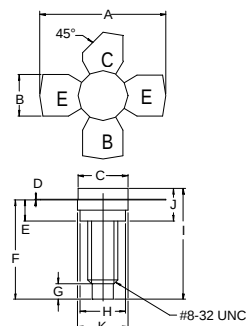
FEATURES:

- $P_g = 10$ dB min. @ 960 MHz
- $P_{1dB} = 1.0$ Watts min. at 960 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	0.25 A
V_{CBO}	40 V
V_{CEO}	28 V
V_{EBO}	3.5 V
P_{DISS}	7.0 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JA}	25°C/W

PACKAGE STYLE .280 4L STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	1.010 / 25.65	1.055 / 26.80
B	.220 / 5.59	.230 / 5.84
C	.270 / 6.86	.285 / 7.24
D	.003 / 0.08	.007 / 0.18
E	.117 / 2.97	.137 / 3.48
F	.572 / 14.53	
G	.130 / 3.30	
H	.245 / 6.22	.255 / 6.48
I	.640 / 16.26	
J	.175 / 4.45	.217 / 5.51
K	.275 / 6.99	.285 / 7.24

ORDER CODE: ASI10577

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 1$ mA	40			V
BV_{CEO}	$I_C = 1$ mA	25			V
BV_{EBO}	$I_E = 1$ mA	3.5			V
I_{CBO}	$V_{CB} = 24$ V			500	μA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 100$ mA	20		120	---
C_{OB}	$V_{CB} = 28$ V $f = 1.0$ MHz			5.0	pF
P_G P_{1dB}	$V_{CC} = 24$ V $I_{CQ} = 125$ mA $f = 960$ MHz	10 1.0			dB W